

CHAPTER 2

2.1

Based upon Table 2.1, a resistivity of $2.83 \mu\Omega\text{-cm} < 1 \text{ m}\Omega\text{-cm}$, and aluminum is a conductor.

2.2

Based upon Table 2.1, a resistivity of $10^{15} \Omega\text{-cm} > 10^5 \Omega\text{-cm}$, and silicon dioxide is an insulator.

2.3

$$I_{\max} = \left(10^7 \frac{A}{\text{cm}^2}\right) (5\mu\text{m}) (1\mu\text{m}) \left(\frac{10^{-8} \text{cm}^2}{\mu\text{m}^2}\right) = 500 \text{ mA}$$

2.4

$$(a) R = \rho \frac{L}{A} = (2.82 \times 10^{-6} \Omega\text{-cm}) \frac{2\sqrt{2} \text{ cm}}{(5 \times 10^{-4} \text{ cm})(1 \times 10^{-4} \text{ cm})} = 160 \Omega$$

$$(b) R = \rho \frac{L}{A} = (2.82 \times 10^{-6} \Omega\text{-cm}) \frac{2\sqrt{2} \text{ cm}}{(5 \times 10^{-4} \text{ cm})(0.5 \times 10^{-4} \text{ cm})} = 319 \Omega$$

2.5

$$(a) R = \rho \frac{L}{A} = (1.66 \times 10^{-6} \Omega\text{-cm}) \frac{2\sqrt{2} \text{ cm}}{(5 \times 10^{-4} \text{ cm})(1 \times 10^{-4} \text{ cm})} = 93.9 \Omega$$

$$(b) R = \rho \frac{L}{A} = (1.66 \times 10^{-6} \Omega\text{-cm}) \frac{2\sqrt{2} \text{ cm}}{(5 \times 10^{-4} \text{ cm})(0.5 \times 10^{-4} \text{ cm})} = 188 \Omega$$

2.6

For silicon, $B = 1.08 \times 10^{31}$ and $E_G = 1.12 \text{ eV}$:

$$n_i = 5.07 \times 10^{-19}/\text{cm}^3 \quad 6.73 \times 10^9/\text{cm}^3 \quad 8.36 \times 10^{13}/\text{cm}^3.$$

For germanium, $B = 2.31 \times 10^{30}$ and $E_G = 0.66 \text{ eV}$:

$$n_i = 2.63 \times 10^{-4}/\text{cm}^3 \quad 2.27 \times 10^{13}/\text{cm}^3 \quad 8.04 \times 10^{15}/\text{cm}^3.$$

2.7

Define an M-File:

```
function f=temp(T)
ni=1E14;
f=ni^2-1.08e31*T^3*exp(-1.12/(8.62e-5*T));
```

$n_i = 10^{13}/\text{cm}^3$ for $T = 436 \text{ K}$ $n_i = 10^{15}/\text{cm}^3$ for $T = 602 \text{ K}$

2.8

$T = 300 \text{ K}$ and $E_G = 1.42 \text{ eV}$: $n_i = 2.21 \times 10^6/\text{cm}^3$

$T = 100 \text{ K}$: $n_i = 6.03 \times 10^{-19}/\text{cm}^3$ $T = 450 \text{ K}$: $n_i = 3.82 \times 10^{10}/\text{cm}^3$

2.9

Define an M-File:

```
function f=temp(T)
f=1e20-1.08e31*T^3*exp(-1.12/(8.62e-5*T));
```

Then: `fzero('temp',300)` | `ans = 305.226 K`

2.10

2.11

2.12

2.13

2.14

$$v_n = -\mu_n E = \left(-1000 \frac{cm^2}{V-s} \right) \left(-2000 \frac{V}{cm} \right) = +2.00 \times 10^6 \frac{cm}{s}$$

$$v_p = +\mu_p E = \left(+400 \frac{cm^2}{V-s} \right) \left(-2000 \frac{V}{cm} \right) = -8.00 \times 10^5 \frac{cm}{s}$$

$$j_n = -q n v_n = \left(-1.60 \times 10^{-19} C \right) \left(10^3 \frac{1}{cm^3} \right) \left(+2.00 \times 10^6 \frac{cm}{s} \right) = -3.20 \times 10^{-10} \frac{A}{cm^2}$$

$$j_p = q p v_p = \left(1.60 \times 10^{-19} C \right) \left(10^{17} \frac{1}{cm^3} \right) \left(-8.00 \times 10^5 \frac{cm}{s} \right) = -1.28 \times 10^4 \frac{A}{cm^2}$$

2.15

$$(a) \quad E = \frac{5V}{10 \times 10^{-4} cm} = 5000 \frac{V}{cm} \quad (b) \quad V = \left(10^5 \frac{V}{cm} \right) (10 \times 10^{-4} cm) = 100 \text{ V}$$

2.16

$$j_p = q p v_p = \left(1.60 \times 10^{-19} C \right) \left(\frac{10^{19}}{cm^3} \right) \left(10^7 \frac{cm}{s} \right) = 1.60 \times 10^7 \frac{A}{cm^2}$$

$$i_p = j_p A = \left(1.60 \times 10^7 \frac{A}{cm^2} \right) (1 \times 10^{-4} cm) (25 \times 10^{-4} cm) = 4.00 \text{ A}$$

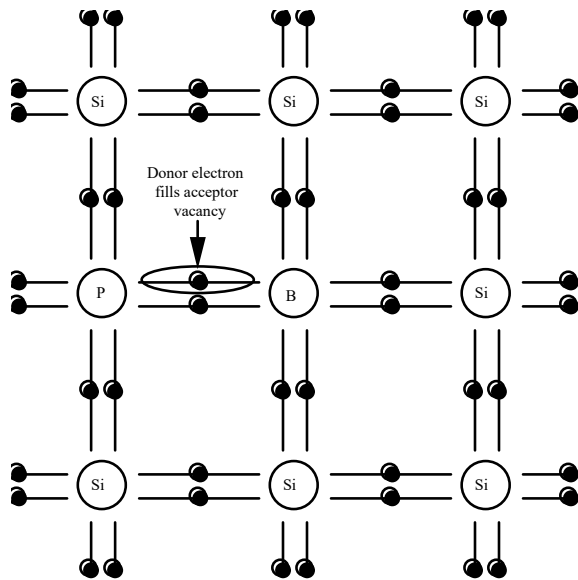
2.17

Using MATLAB as in Problem 2.5 yields $T \leq 316.6$ K.

2.18

This is a transcendental equation and must be solved numerically by iteration. Using the HP solver routine or a spread sheet yields $T \geq 2701$ K. Note that this temperature is far above the melting temperature of silicon.

2.19



No free electrons or holes (except those corresponding to n_i).

2.20

Since Ge is from column IV, acceptors come from column III and donors come from column V. (a) Acceptors: B, Al, Ga, In, Tl (b) Donors: N, P, As, Sb, Bi

2.21

(a) Gallium is from column 3 and silicon is from column 4. Thus silicon has an extra electron and will act as a donor impurity.
 (b) Arsenic is from column 5 and silicon is from column 4. Thus silicon is deficient in one electron and will act as an acceptor impurity.

2.22

(a) Germanium is from column IV and indium is from column III. Thus germanium has one extra electron and will act as a donor impurity.
 (b) Germanium is from column IV and phosphorus is from column V. Thus germanium has one less electron and will act as an acceptor impurity.

2.23

2.24

2.25

$$N = \left(\frac{10^{16} \text{ atoms}}{\text{cm}^3} \right) (0.5 \mu\text{m}) (5 \mu\text{m}) (0.5 \mu\text{m}) \left(\frac{10^{-4} \text{ cm}}{\mu\text{m}} \right)^3 = 12,500 \text{ atoms}$$

2.26

(a) Since arsenic is a donor, $N_D = 3 \times 10^{17}/\text{cm}^3$. Assume $N_A = 0$, since it is not specified. The material is n-type.

(c) At 250K, $n_i^2 = 1.08 \times 10^{31} (250)^3 \exp\left(-\frac{1.12}{8.62 \times 10^{-5} (250)}\right) = 4.53 \times 10^{15} / \text{cm}^6$

$$n_i = 6.73 \times 10^7 / \text{cm}^3 \quad N_D - N_A \gg 2n_i, \text{ so } n = 3 \times 10^{17} / \text{cm}^3 \text{ and } n = \frac{4.53 \times 10^{15}}{3 \times 10^{17}} = 0.0151 / \text{cm}^3$$

2.27

(a) Since boron is an acceptor, $N_A = 6 \times 10^{18}/\text{cm}^3$. Assume $N_D = 0$, since it is not specified. The material is p-type.

(c) At 200K, $n_i^2 = 1.08 \times 10^{31} (200)^3 \exp\left(-\frac{1.12}{8.62 \times 10^{-5} (200)}\right) = 5.28 \times 10^9 / \text{cm}^6$

$$n_i = 7.27 \times 10^4 / \text{cm}^3 \quad N_A - N_D \gg 2n_i, \text{ so } p = 6 \times 10^{18} / \text{cm}^3 \text{ and } n = \frac{5.28 \times 10^9}{6 \times 10^{18}} = 8.80 \times 10^{-10} / \text{cm}^3$$

2.28

(a) Arsenic is a donor, and boron is an acceptor. $N_D = 2 \times 10^{18}/\text{cm}^3$, and $N_A = 8 \times 10^{18}/\text{cm}^3$. Since $N_A > N_D$, the material is p-type.

2.29

(a) Phosphorus is a donor, and boron is an acceptor. $N_D = 2 \times 10^{17}/\text{cm}^3$, and $N_A = 5 \times 10^{17}/\text{cm}^3$. Since $N_A > N_D$, the material is p-type.

2.30

2.31

2.32

2.33

$N_D = 5 \times 10^{16}/\text{cm}^3$. Assume $N_A = 0$, since it is not specified.

2.34

$N_A = 2.5 \times 10^{18}/\text{cm}^3$. Assume $N_D = 0$, since it is not specified.

2.35

Indium is from column 3 and is an acceptor. $N_A = 8 \times 10^{19}/\text{cm}^3$. Assume $N_D = 0$, since it is not specified.

2.36

2.37

An iterative solution is required. Using Fig. 2.8:

N_A	μ_p	$\mu_p p$
10^{18}	100	1.0×10^{20}
1.1×10^{18}	100	1.1×10^{20}
1.2×10^{17}	95	1.14×10^{20}
1.3×10^{19}	90	1.17×10^{20}

2.38

An iterative solution is required. Using the equations in Fig. 2.8:

N_D	μ_n	$\mu_n n$
10^{16}	1250	1.25×10^{19}
10^{18}	264	2.64×10^{20}
10^{17}	802	8.02×10^{19}
1.2×10^{17}	604	1.21×10^{20}
1.85×10^{19}	626	1.16×10^{20}

2.39

An iterative solution is required. Using the equations in Fig. 2.8:

N_A	μ_p	$\mu_p p$
10^{18}	96.7	9.67×10^{20}
1.1×10^{18}	93.7	1.03×10^{20}
1.2×10^{17}	91.0	1.09×10^{20}
1.3×10^{19}	88.7	1.15×10^{20}

2.40

An iterative solution is required. Using the equations in Fig. 2.8:

N_A	μ_p	$\mu_p p$
10^{16}	406	4.06×10^{18}
2×10^{16}	363	7.26×10^{18}
3×10^{16}	333	9.99×10^{18}
4×10^{16}	310	1.24×10^{19}

2.41

Yes, by adding equal amounts of donor and acceptor impurities the mobilities are reduced, but the hole and electron concentrations remain unchanged. See Problem 2.44 for example. However, it is physically impossible to add exactly equal amounts of the two impurities.

2.42

An iterative solution is required. Using the equations in Fig. 2.8:

N_D	μ_n	$\mu_n n$
10^{15}	1350	1.35×10^{18}
1.5×10^{15}	1340	2.01×10^{18}
1.6×10^{15}	1340	2.14×10^{18}
1.55×10^{15}	1340	2.08×10^{18}

2.43 (a)

An iterative solution is required. Using the equations in Fig. 2.8:

N_D	μ_n	$\mu_n n$
10^{19}	116	1.16×10^{21}
7×10^{19}	96.1	6.73×10^{21}
6.5×10^{19}	96.4	6.27×10^{21}

(b)

An iterative solution is required using the equations in Fig. 2.8:

N_A	μ_p	$\mu_p p$
1×10^{20}	49.6	4.96×10^{21}
1.2×10^{20}	49.4	5.93×10^{21}
1.25×10^{20}	49.4	6.17×10^{21}
1.26×10^{20}	49.4	6.22×10^{21}

2.44

Based upon the value of its resistivity, the material is an insulator. However, it is not intrinsic because it contains impurities. Addition of the impurities has increased the resistivity.

2.45

(a) For the 1 ohm-cm starting material:

An iterative solution is required. Using the equations in Fig. 2.8:

N_A	μ_p	$\mu_p p$
10^{16}	406	4.1×10^{18}
1.5×10^{16}	383	5.7×10^{18}
1.7×10^{16}	374	6.4×10^{19}

To change the resistivity to 0.25 ohm-cm:

-

N_A	μ_p	$\mu_p p$
6×10^{16}	276	1.7×10^{19}
8×10^{16}	233	2.3×10^{19}
1.1×10^{17}	225	2.5×10^{19}

Additional acceptor concentration = $1.1 \times 10^{17} - 1.7 \times 10^{16} = 9.3 \times 10^{16}/\text{cm}^3$

(b) If donors are added:

N_D	$N_D + N_A$	μ_n	$N_D - N_A$	$\mu_n n$
2×10^{16}	3.7×10^{16}	1060	3×10^{15}	3.2×10^{18}
1×10^{17}	1.2×10^{17}	757	8.3×10^{16}	6.3×10^{19}
8×10^{16}	9.7×10^{16}	811	6.3×10^{16}	5.1×10^{19}
4.1×10^{16}	5.8×10^{16}	950	2.4×10^{16}	2.3×10^{19}

So $N_D = 4.1 \times 10^{16}/\text{cm}^3$ must be added to change achieve a resistivity of 0.25 ohm-cm. The silicon is converted to n-type material.

2.46

Phosphorus is a donor: $N_D = 10^{16}/\text{cm}^3$ and $\mu_n = 1250 \text{ cm}^2/\text{V-s}$ from Fig. 2.8.

Now we add acceptors until $\sigma = 5.0 (\Omega\text{-cm})^{-1}$:

N_A	$N_D + N_A$	μ_p	$N_A - N_D$	$\mu_p p$
1.00E+17	1.10E+17	2.25E+02	9.00E+16	2.02E+19
2.00E+17	2.10E+17	1.76E+02	1.90E+17	3.34E+19
1.50E+17	1.60E+17	1.95E+02	1.40E+17	2.74E+19
1.40E+17	1.50E+17	2.00E+02	1.30E+17	2.60E+19
1.30E+17	1.40E+17	2.06E+02	1.20E+17	2.47E+19
1.32E+17	1.42E+17	2.05E+02	1.22E+17	2.50E+19

2.47

Boron is an acceptor: $N_A = 10^{16}/\text{cm}^3$ and $\mu_p = 405 \text{ cm}^2/\text{V-s}$ from Fig. 2.8.

Now we add donors until $\sigma = 5.5 (\Omega\text{-cm})^{-1}$:

N_D	$N_D + N_A$	μ_n	$N_D - N_A$	$\mu_p p$
8×10^{16}	9×10^{16}	832	7×10^{16}	5.8×10^{19}
6×10^{16}	7×10^{16}	901	5×10^{16}	4.5×10^{19}
4.5×10^{16}	5.5×10^{16}	964	3.5×10^{16}	3.4×10^{19}

2.48

T (K)	50	75	100	150	200	250	300	350	400
V_T (mV)	4.31	6.46	8.61	12.9	17.2	21.5	25.8	30.1	34.5

2.49

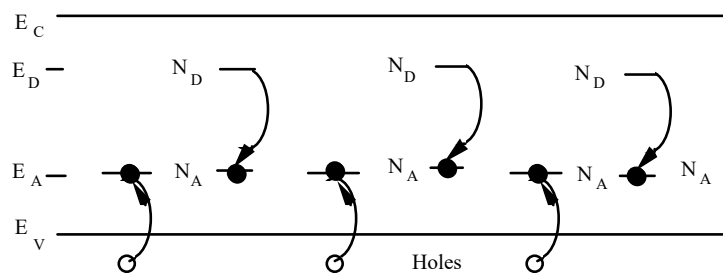
2.50

2.51

2.52

At $x = 0$:

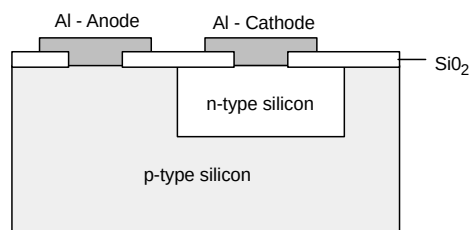
2.53 $N_A = 2N_D$



2.54

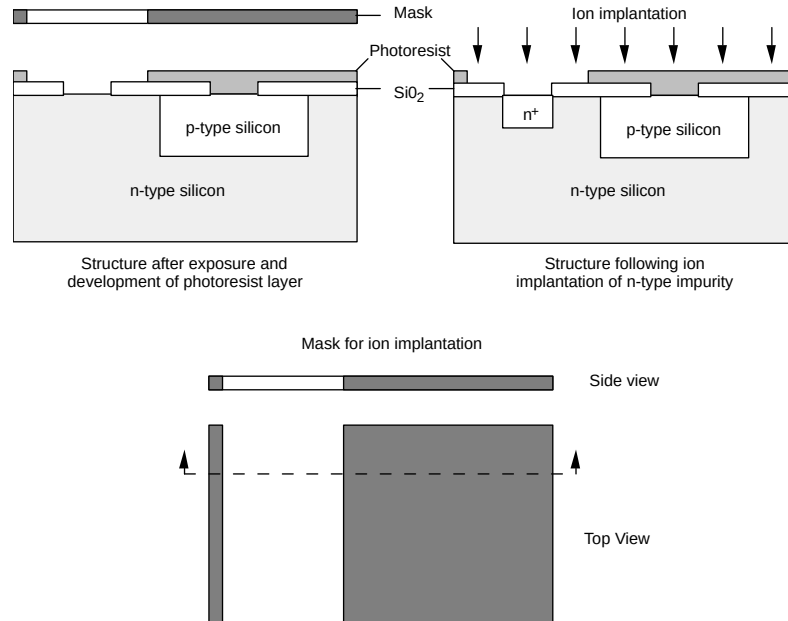
$$\lambda = \frac{hc}{E} = \frac{(6.626 \times 10^{-34} \text{ J} \cdot \text{s})(3 \times 10^8 \text{ m/s})}{(1.12 \text{ eV})(1.602 \times 10^{-19} \text{ J/eV})} = 1.108 \text{ } \mu\text{m}$$

2.55



2.56

An n-type ion implantation step could be used to form the n^+ region following step (f) in Fig. 2.17. A mask would be used to cover up the opening over the p-type region and leave the opening over the n-type silicon. The masking layer for the implantation could just be photoresist.



2.57